AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A power semiconductor module with a housing ~~(1)~~ comprising:

a hardenable plastic casting compound and a base plate ~~(2)~~, wherein electric power semiconductor components ~~(4)~~ are arranged on a section of the surface of the base plate ~~(2)~~ that faces the housing ~~(1)~~ by means of an insulating layer ~~(5)~~, wherein at least the section of the surface of the base plate ~~(2)~~ that faces the housing ~~(1)~~ and contains the electric power semiconductor components ~~(4)~~ is encapsulated in the housing ~~(1)~~, and wherein the hardenable plastic casting compound has a hardness between 30 and 95 ShoreA, ~~characterized in that~~ and wherein the hardenable plastic casting compound includes a thermoplastic hot-melt adhesive.

2. (Currently Amended) The power semiconductor module according to Claim 1, ~~characterized in that~~ wherein the hardenable plastic casting compound has a coefficient of linear expansion between 40 and 300 ppm/°K and a flexural modulus between 100 kPa and 2 GPa.

3. (Currently Amended) The power semiconductor module according to Claim 1, ~~characterized in that~~ wherein the hot-melt adhesive contains a dimeric fatty acid polyamide.

4. (Currently Amended) The power semiconductor module according to ~~one of Claims~~ Claim 1 ~~-3~~, ~~characterized in that~~ wherein the hot-melt adhesive has a casting temperature between 150 °C and 220 °C.

5. (Currently Amended) The power semiconductor module according to ~~one of Claims~~ Claim 1[[-4]], ~~characterized in that~~ wherein the hot-melt adhesive can be cast with a casting pressure between 0.1 MPa and 0.5 MPA.

6. (Currently Amended) The power semiconductor module according to ~~one of the preceding claims~~ Claim 1, ~~characterized in that~~ wherein the hardenable plastic casting compound is essentially transparent in the hardened state.

7. (Currently Amended) The power semiconductor module according to ~~one of the preceding claims~~ Claim 1, ~~characterized in that~~ wherein the electric power semiconductor components ~~(4)~~ are essentially arranged directly on the surface of the base plate ~~(2)~~ that faces the housing ~~(1)~~ rather than via the insulating layer ~~(5)~~.

8. (Currently Amended) The power semiconductor module according to Claim 1, ~~characterized in that~~ wherein a control device ~~(6)~~ is connected to at least one of the electric power semiconductor components ~~(4)~~ and at least partially encapsulated in the housing ~~(1)~~.

9. (Currently Amended) The power semiconductor module according to Claim 8, ~~characterized in that~~ wherein the control device ~~(6)~~ contains a printed circuit board ~~(7)~~ with a first circuit board side ~~(8)~~ that faces the electric power semiconductor components ~~(4)~~ and a second circuit board side ~~(9)~~ that faces away from the electric power semiconductor components ~~(4)~~, ~~in that~~ wherein the first circuit board side ~~(8)~~ is encapsulated in the housing ~~(1)~~, and ~~in that~~ wherein the second circuit board side ~~(9)~~ lies outside the housing ~~(1)~~.

10. (Currently Amended) The power semiconductor module according to Claim 9, ~~characterized in that~~ wherein the second circuit board side ~~(9)~~ is thermally coupled with a cooling element ~~(10)~~.

11. (Currently Amended) The power semiconductor module according to Claim 8, ~~characterized in that~~ wherein control link elements ~~(11)~~ connected to the control device ~~(6)~~ are encapsulated in the housing ~~(1)~~ and the terminal ends of the control link elements ~~(11)~~ lead out of the housing ~~(1)~~.

12. (Currently Amended) The power semiconductor module according to Claim 11, ~~characterized in that~~ wherein the control link elements ~~(11)~~ are realized in the form of cables.

13. (Currently Amended) The power semiconductor module according to Claim 1, ~~characterized in that~~ wherein at least one power link element ~~(3)~~ is connected to at least one of the electric power semiconductor components ~~(4)~~ and

encapsulated in the housing ~~(1)~~, wherein a terminal end of the at least one power link element ~~(3)~~ leads out of the housing ~~(1)~~, and ~~in that the~~ wherein at least one power link element ~~(3)~~ is realized in the form of a cable.